

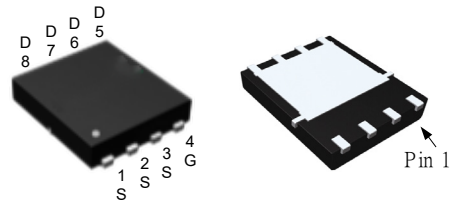
Features

- 30V/130A
 $R_{DS(ON)}=1.35m\Omega(\text{typ.})@V_{GS}=10V$
 $R_{DS(ON)}=1.9\text{ m}\Omega(\text{typ.})@V_{GS}=4.5V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)
- Moisture Sensitivity Level MSL1
(per JEDEC J-STD-020D)

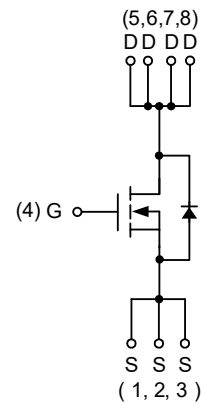
Applications

- For E-cigrate Application.
- For Auto Model Airplane.
- Synchronous Rectifier for Server.

Pin Description



DFN5x6A-8_EP



N-Channel MOSFET

Absolute Maximum Ratings (T_A=25°C Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _C =25°C	130	A
I _D	Continuous Drain Current	T _C =25°C	130	A
		T _C =100°C	98	
I _{DM} ^b	Pulsed Drain Current	T _C =25°C	390	
P _D	Maximum Power Dissipation	T _C =25°C	43.1	W
		T _C =100°C	17.2	
R _{θJC}	Thermal Resistance-Junction to Case	Steady State	2.9	°C/W
R _{θJA} ^c	Thermal Resistance-Junction to Ambient	t ≤ 10s	19.5	°C/W
		Steady State	55	
I _{AS} ^d	Avalanche Current, Single pulse	L=0.1mH	46	A
E _{AS} ^d	Avalanche Energy, Single pulse	L=0.1mH	106	mJ

Note a : Calculated continuous current based on maximum allowable junction temperature. Bonding wire limitation current is 100A.

Note b : Pulse width limited by maximum junction temperature.

Note c : Surface mounted on 1in² pad area, steady state t = 999s.

Note d : UIS tested and pulse width limited by maximum junction temperature (initial temperature T_J=25°C).

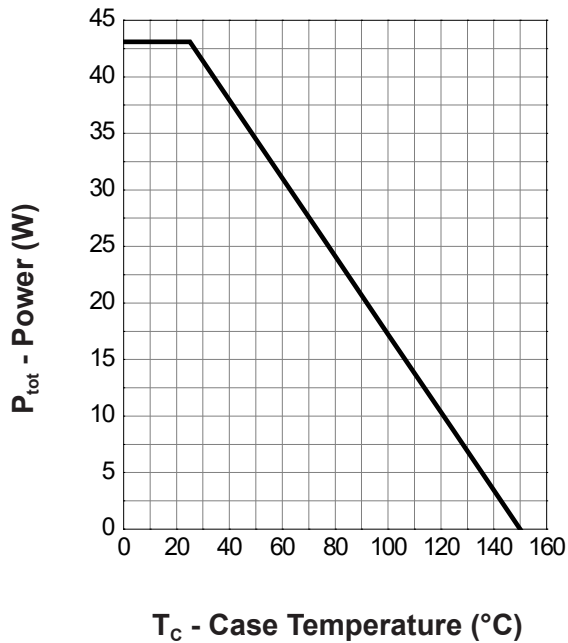
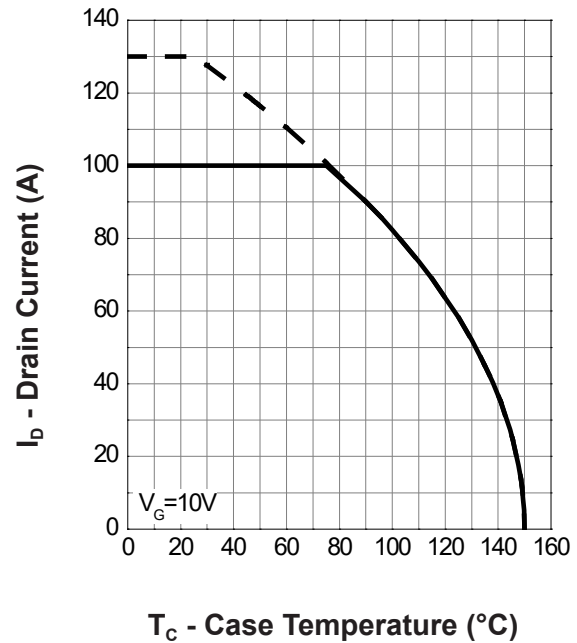
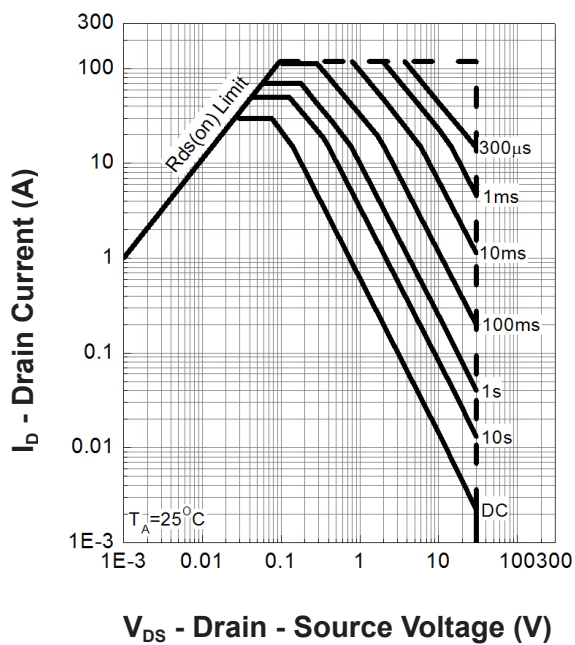
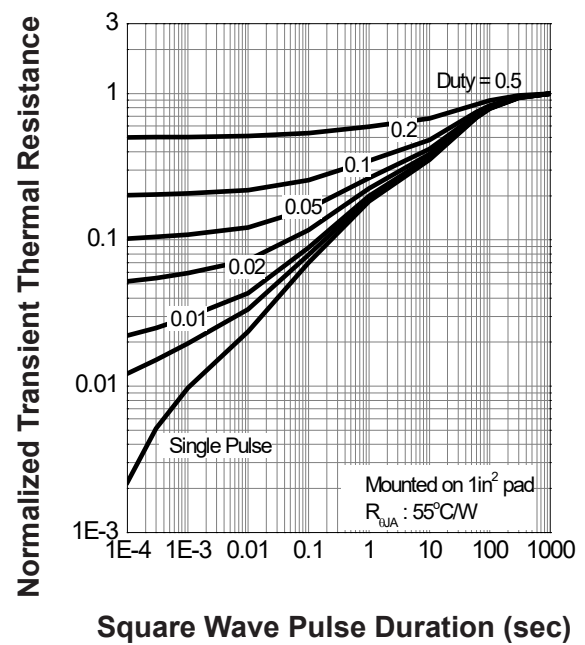
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.0	1.8	2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^e	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =20A	-	1.35	1.6	mΩ
		V _{GS} =4.5V, I _{DS} =15A	-	1.9	2.5	
G _{fs}	Forward Transconductance	V _{DS} =5V, I _{DS} =15A	-	41	-	S
Diode Characteristics						
V _{SD} ^e	Diode Forward Voltage	I _{SD} =20A, V _{GS} =0V	-	0.77	1.1	V
t _{rr}	Reverse Recovery Time	I _{SD} =20A, dI _{SD} /dt=100A/μs	-	40.5	-	ns
t _a	Charge Time		-	20.7	-	
t _b	Discharge Time		-	19.8	-	
Q _{rr}	Reverse Recovery Charge		-	30.3	-	nC
Dynamic Characteristics ^f						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	1.1	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz	-	3170	4121	pF
C _{oss}	Output Capacitance		-	1215	-	
C _{rss}	Reverse Transfer Capacitance		-	70	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, R _L =15Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	18	33	ns
t _r	Turn-on Rise Time		-	12	22	
t _{d(OFF)}	Turn-off Delay Time		-	54	98	
t _f	Turn-off Fall Time		-	70	126	
Gate Charge Characteristics ^f						
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _{DS} =20A	-	34.5	48	nC
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _{DS} =20A	-	17.8	-	
Q _{gth}	Threshold Gate Charge		-	3.3	-	
Q _{gs}	Gate-Source Charge		-	6	-	
Q _{gd}	Gate-Drain Charge		-	6.8	-	

Note e : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

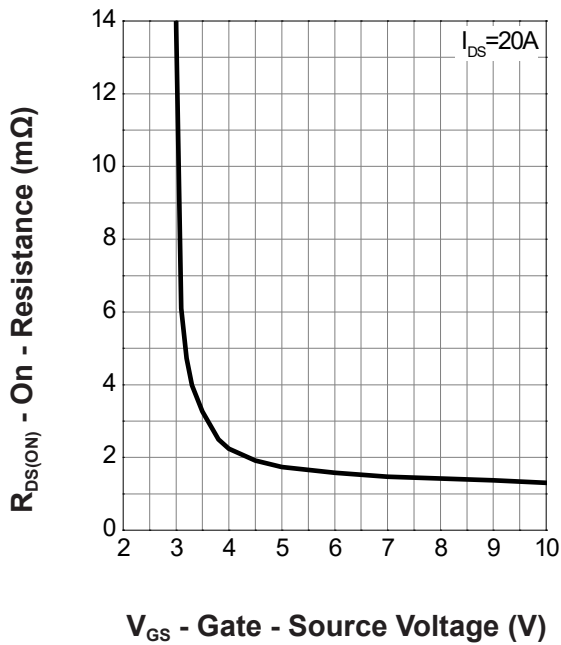
Note f : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

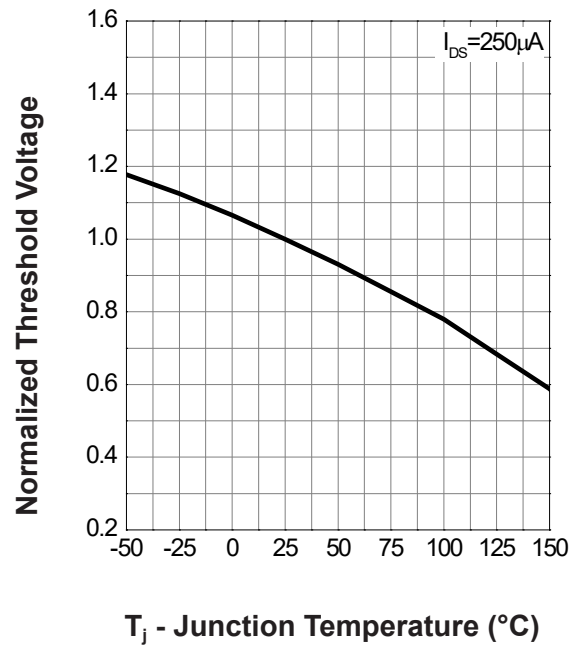
Power Dissipation

Drain Current

Safe Operation Area

Thermal Transient Impedance


Typical Operating Characteristics(Cont.)

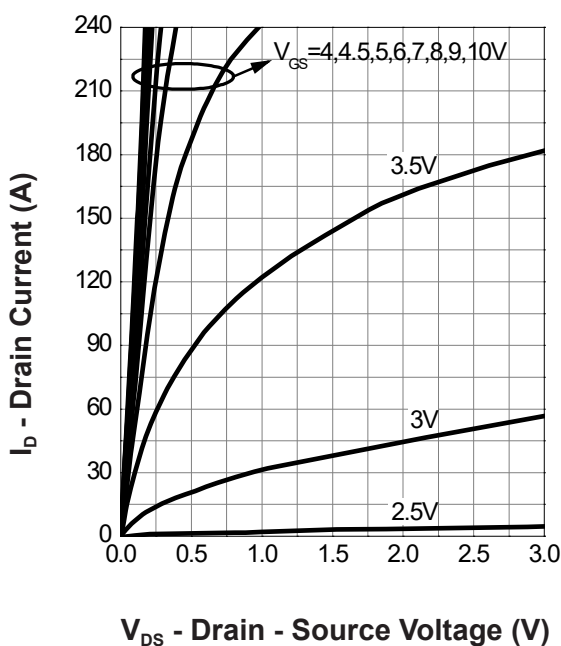
Gate-Source On Resistance



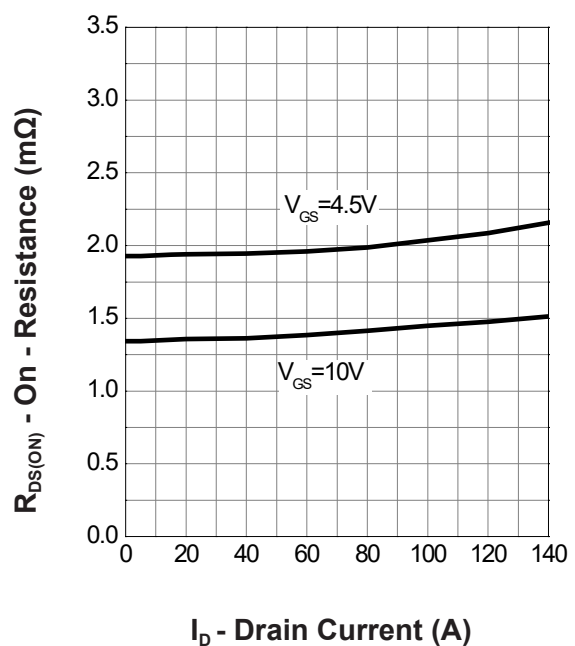
Gate Threshold Voltage



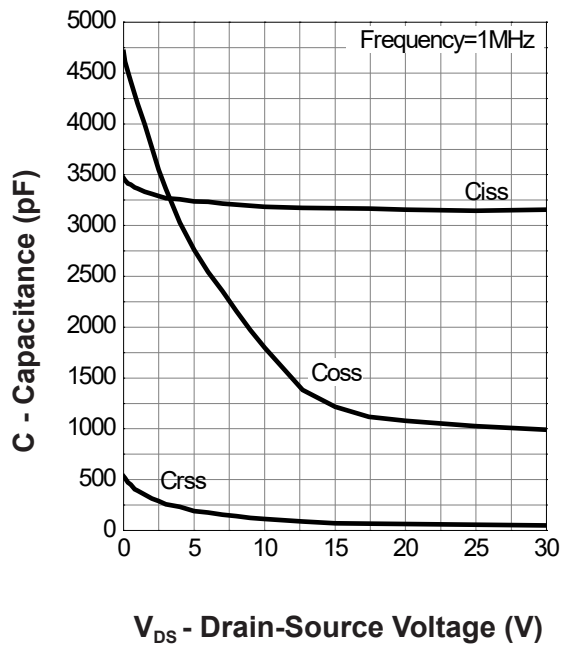
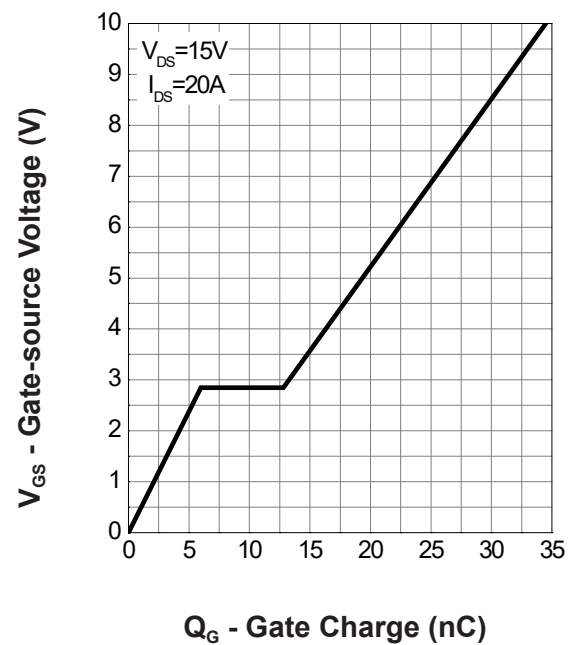
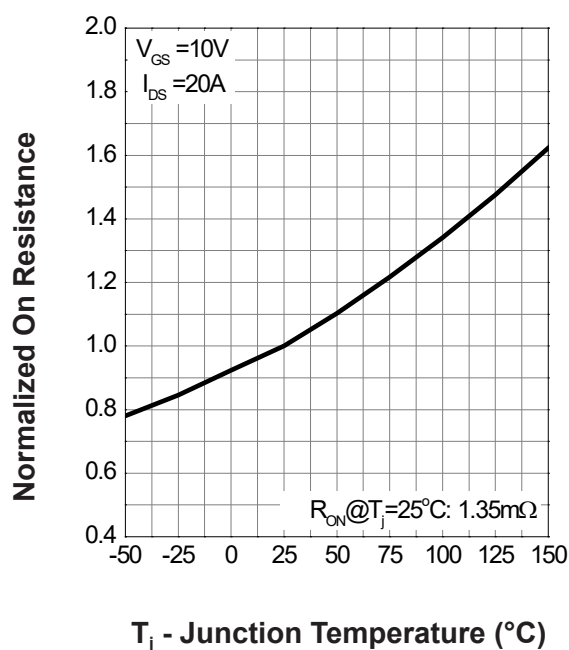
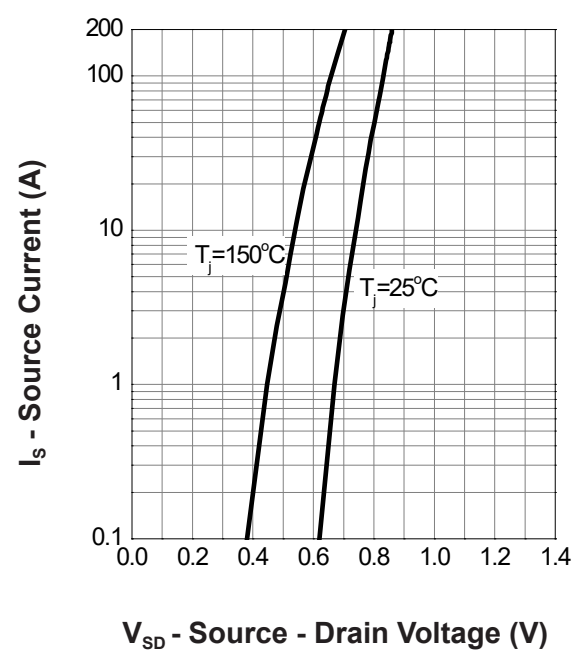
Output Characteristics



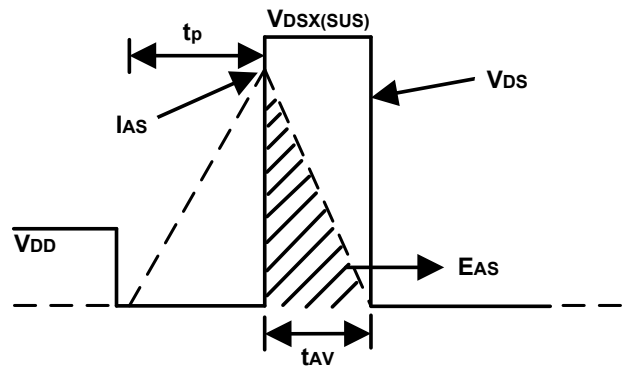
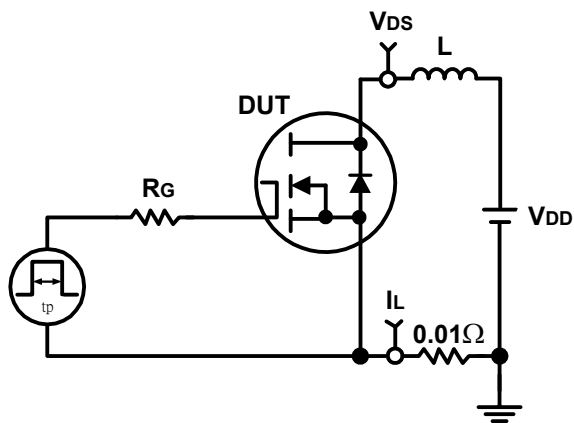
Drain-Source On Resistance



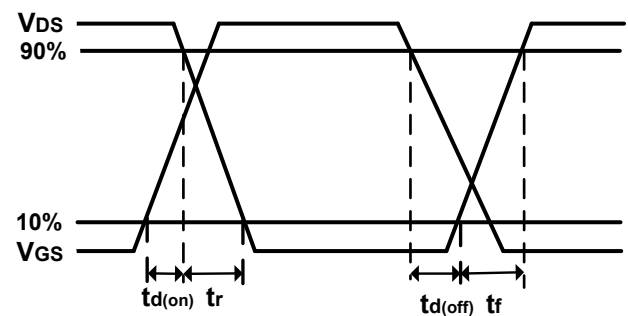
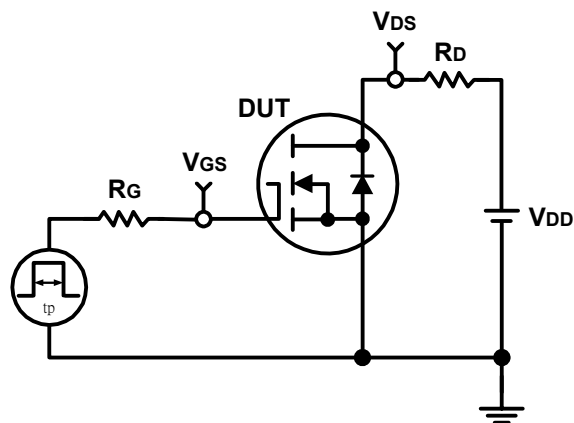
Typical Operating Characteristics(Cont.)

Capacitance

Gate Charge

Drain-Source On Resistance

Source-Drain Diode Forward


Avalanche Test Circuit and Waveforms

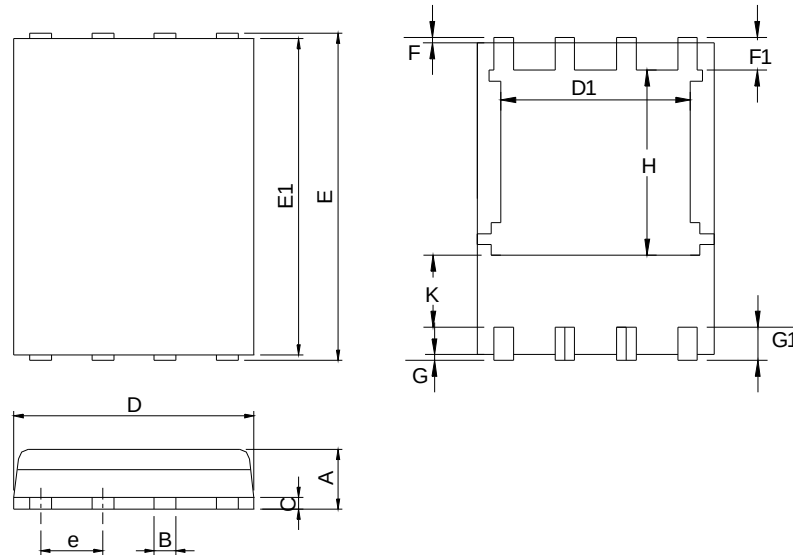


Switching Time Test Circuit and Waveforms



Package Information

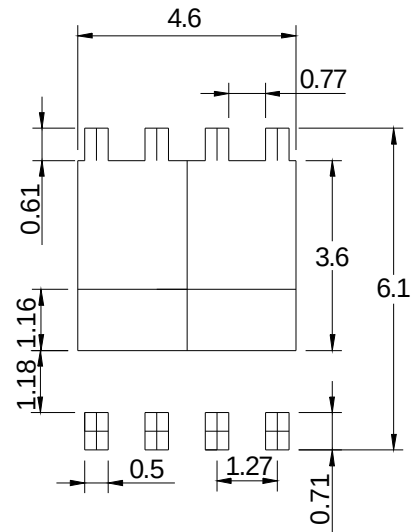
DFN5x6-8



SYMBOL	DFN5x6-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.90	1.20	0.035	0.047
B	0.3	0.51	0.012	0.020
C	0.19	0.25	0.007	0.010
D	4.80	5.30	0.189	0.209
D1	4.00	4.40	0.157	0.173
E	5.90	6.20	0.232	0.244
E1	5.50	5.80	0.217	0.228
e	1.27 BSC		0.050 BSC	
F	0.05	0.30	0.002	0.012
F1	0.35	0.75	0.014	0.030
G	0.05	0.30	0.002	0.012
G1	0.35	0.75	0.014	0.030
H	3.34	3.9	0.131	0.154
K	0.762	-	0.03	-

Note : 1.Dimension D, D1,D2 and E1 do not include mold flash or protrusions.
Mold flash or protrusions shall not exceed 10 mil.

RECOMMENDED LAND PATTERN



UNIT: mm